

Silicon Tuning Diode

These devices are designed in the popular Plastic Surface Mount Package for high volume requirements of FM Radio and TV tuning and AFC, general frequency control and tuning applications. They provide solid-state reliability in replacement of mechanical tuning methods.

Features

- High Q
- Controlled and Uniform Tuning Ratio
- Standard Capacitance Tolerance – 10%
- Complete Typical Design Curves
- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	30	Vdc
Peak Forward Current	I_F	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, $T_A = 25^\circ\text{C}$ (Note 1) Derate above 25°C	P_D	200 1.57	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	635	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

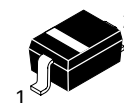
1. FR-4 Minimum Pad



ON Semiconductor®

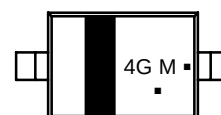
<http://onsemi.com>

30 VOLTS VOLTAGE VARIABLE CAPACITANCE DIODE



PLASTIC
SOD-323
CASE 477
STYLE 1

MARKING DIAGRAM



4G = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMVL2101T1	SOD-323	3000 / Tape & Reel
MMVL2101T1G	SOD-323 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMVL2101T1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I _R = 10 µAdc)	V _{(BR)R}	30	–	–	Vdc
Reverse Voltage Leakage Current (V _R = 25 Vdc, T _A = 25°C)	I _R	–	–	0.1	µAdc
Diode Capacitance Temperature Coefficient (V _R = 4.0 Vdc, f = 1.0 MHz)	TC _C	–	280	–	ppm/°C

Device	C _T , Diode Capacitance V _R = 4.0 Vdc, f = 1.0 MHz pF			Q, Figure of Merit V _R = 4.0 Vdc, f = 50 MHz	TR, Tuning Ratio C ₂ /C ₃₀ f = 1.0 MHz		
	Min	Nom	Max	Typ	Min	Typ	Max
MMVL2101T1	6.1	6.8	7.5	450	2.5	2.7	3.2

PARAMETER TEST METHODS

1. C_T, DIODE CAPACITANCE

(C_T = C_C + C_J). C_T is measured at 1.0 MHz using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

2. TR, TUNING RATIO

TR is the ratio of C_T measured at 2.0 Vdc divided by C_T measured at 30 Vdc.

3. Q, FIGURE OF MERIT

Q is calculated by taking the G and C readings of an admittance bridge at the specified frequency and substituting in the following equations:

$$Q = \frac{2\pi fC}{G}$$

(Boonton Electronics Model 33AS8 or equivalent). Use Lead Length ≈ 1/16".

4. TC_C, DIODE CAPACITANCE TEMPERATURE COEFFICIENT

TC_C is guaranteed by comparing C_T at V_R = 4.0 Vdc, f = 1.0 MHz, T_A = -65°C with C_T at V_R = 4.0 Vdc, f = 1.0 MHz, T_A = +85°C in the following equation, which defines TC_C:

$$TC_C = \left| \frac{C_T(+85^\circ\text{C}) - C_T(-65^\circ\text{C})}{85 + 65} \right| \cdot \frac{10^6}{C_T(25^\circ\text{C})}$$

Accuracy limited by measurement of C_T to ±0.1 pF.

TYPICAL DEVICE CHARACTERISTICS

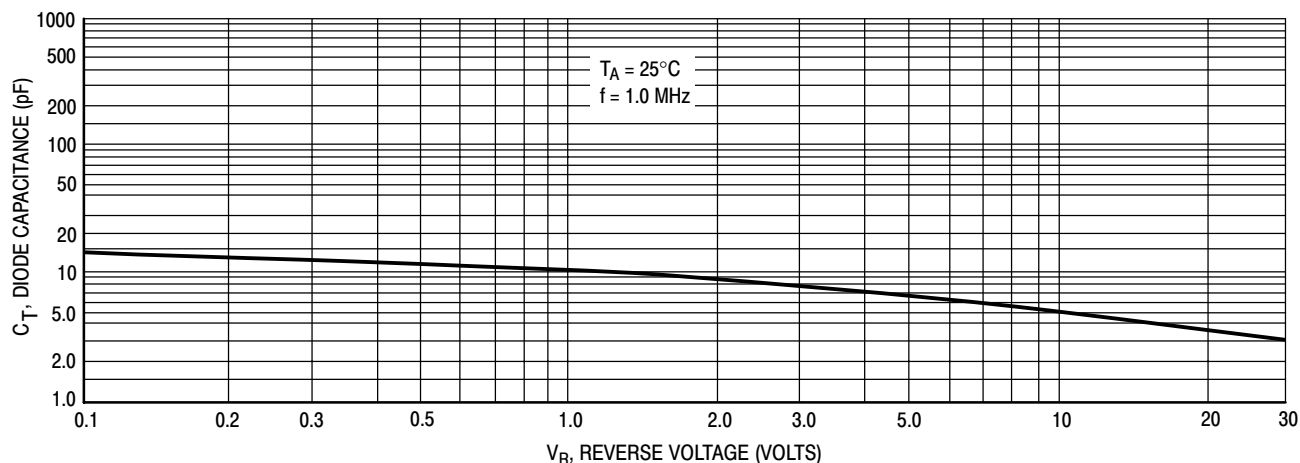


Figure 1. Diode Capacitance versus Reverse Voltage

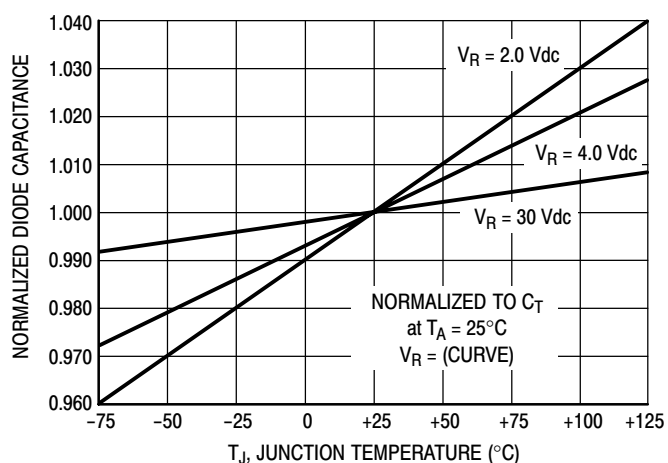


Figure 2. Normalized Diode Capacitance versus Junction Temperature

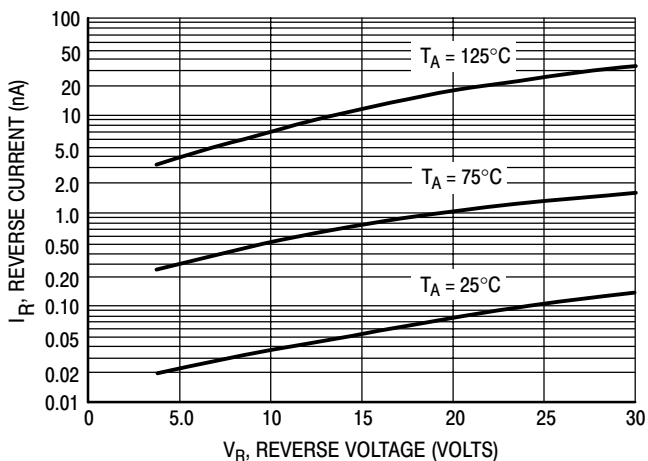


Figure 3. Reverse Current versus Reverse Bias Voltage

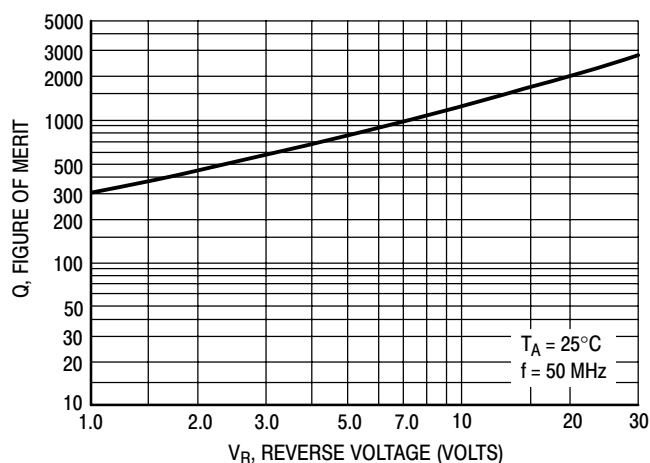


Figure 4. Figure of Merit versus Reverse Voltage

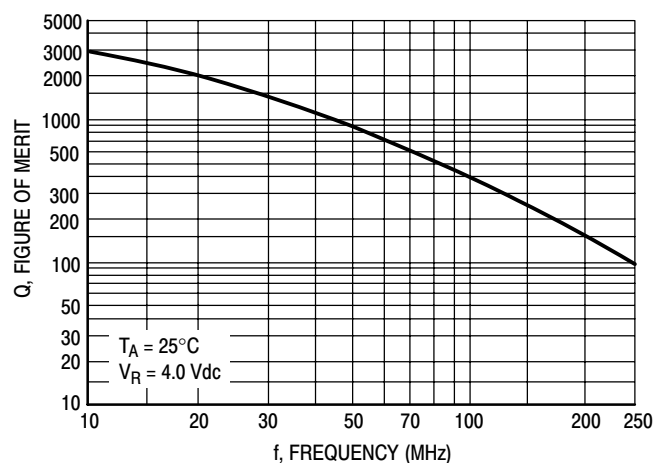


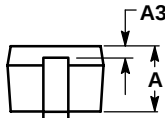
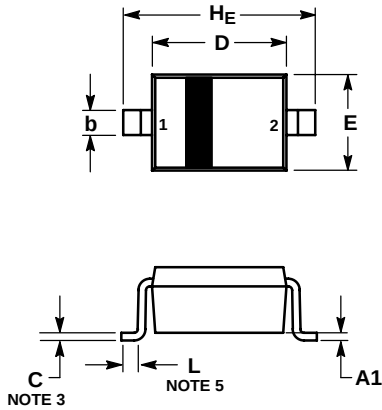
Figure 5. Figure of Merit versus Frequency

MMVL2101T1

[查询"MMVL2101T1G"供应商](#)

PACKAGE DIMENSIONS

SOD-323
CASE 477-02
ISSUE G



NOTES:

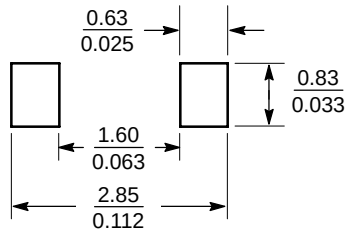
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.30	2.50	2.70	0.090	0.098	0.105

STYLE 1:

1. CATHODE
2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.

MMVL2101T1/D